# 2SB1503

## Silicon PNP epitaxial planar type Darlington

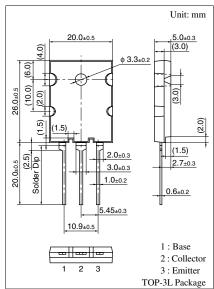
For power amplification Complementary to 2SD2276

#### ■ Features

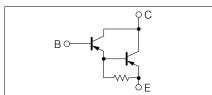
- Optimum for 110 W Hi-Fi output
- $\bullet$  High forward current transfer ratio  $h_{FE}$ : 5 000 to 30 000
- $\bullet$  Low collector to emitter saturation voltage  $V_{CE(sat)}$ : < -2.5 V

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter		Symbol	Rating	Unit
Collector to base voltage		$V_{CBO}$	-160	V
Collector to emitter voltage		$V_{CEO}$	-140	V
Emitter to base voltage		$V_{EBO}$	-5	V
Peak collector current		$I_{CP}$	-12	A
Collector current		$I_C$	-7	A
Collector power	$T_C = 25^{\circ}C$	$P_{C}$	120	W
dissipation	$T_a = 25^{\circ}C$		3.5	
Junction temperature		$T_{j}$	150	°C
Storage temperature		$T_{stg}$	-55 to +150	°C



#### **Internal Connection**



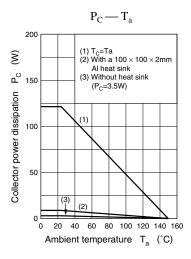
### ■ Electrical Characteristics $T_C = 25$ °C

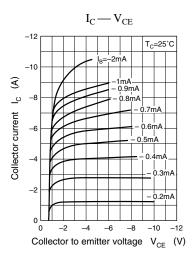
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -160 \text{ V}, I_E = 0$			-100	μΑ
	$I_{CEO}$	$V_{CE} = -140 \text{ V}, I_B = 0$			-100	μΑ
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-100	μΑ
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = -30 \text{ mA}, I_{\rm B} = 0$	-140			V
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ A}$	2 000			
	h <sub>FE2</sub> *	$V_{CE} = -5 \text{ V}, I_{C} = -7 \text{ A}$	5 000		30 000	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -7 \text{ A}, I_{\rm B} = -7 \text{ mA}$			-2.5	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = -7 \text{ A}, I_{\rm B} = -7 \text{ mA}$			-3.0	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_{C} = -0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	t <sub>on</sub>	$I_C = -7 \text{ A}, I_{B1} = -7 \text{ mA}, I_{B2} = 7 \text{ mA},$		1.0		μs
Storage time	t <sub>stg</sub>	$V_{CC} = -50 \text{ V}$		1.5		μs
Fall time	$t_{\rm f}$			1.2		μs

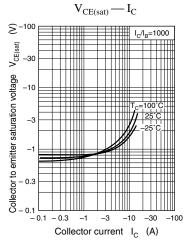
Note) \*: Rank classification

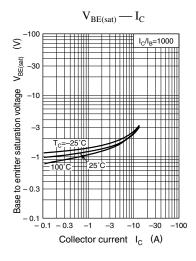
Rank	Q	S	Р
h <sub>FE2</sub>	5 000 to 15 000	7 000 to 21 000	8 000 to 30 000

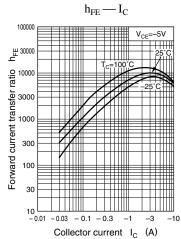
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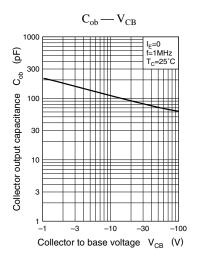


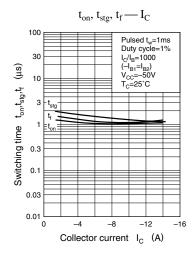


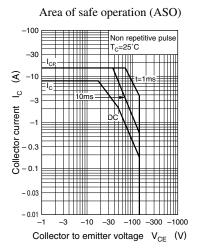






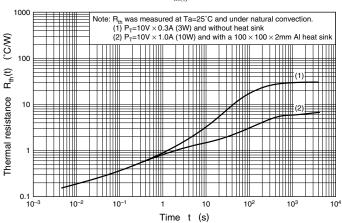






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